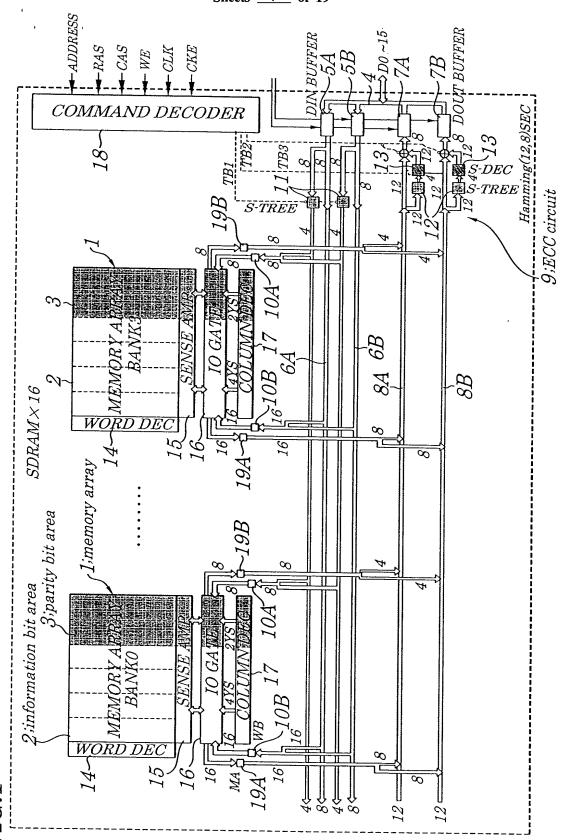
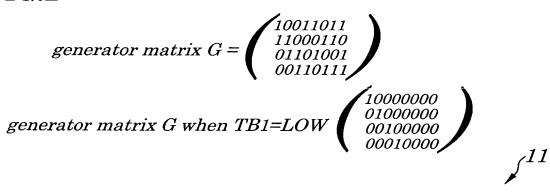
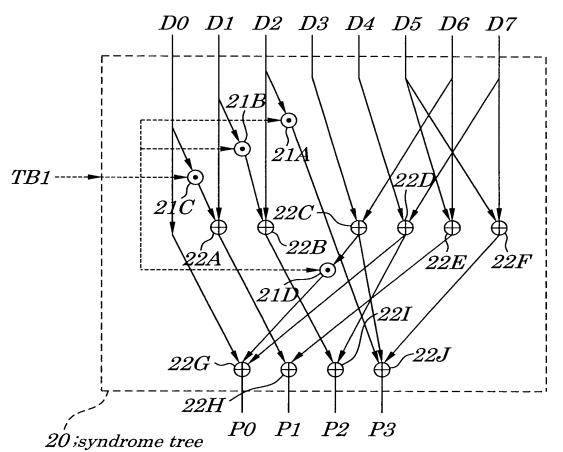
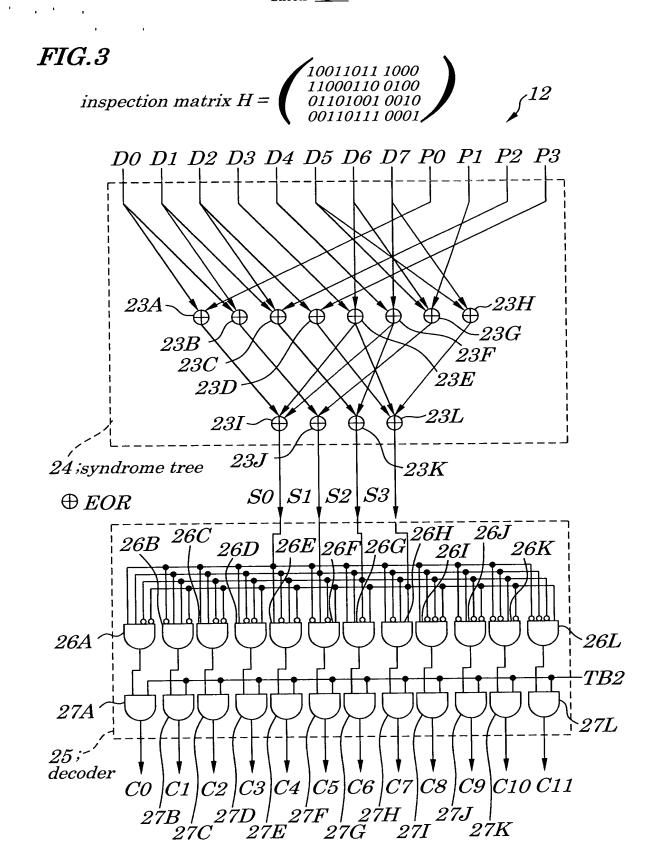
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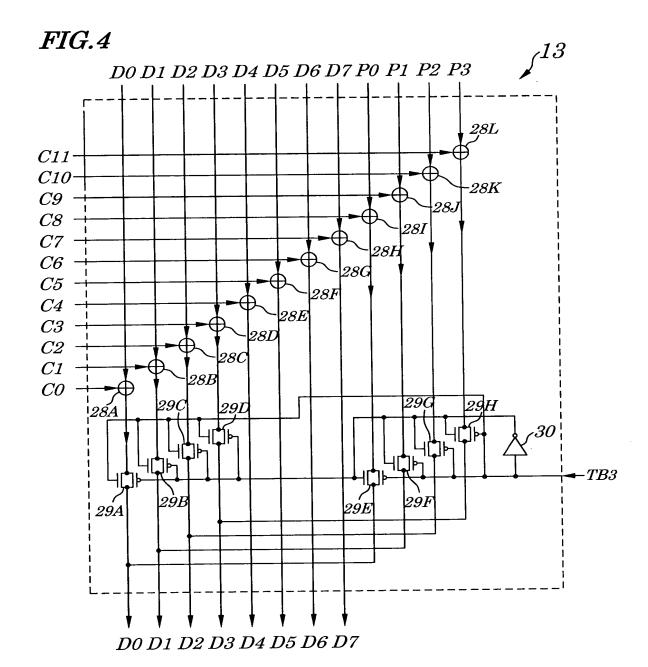




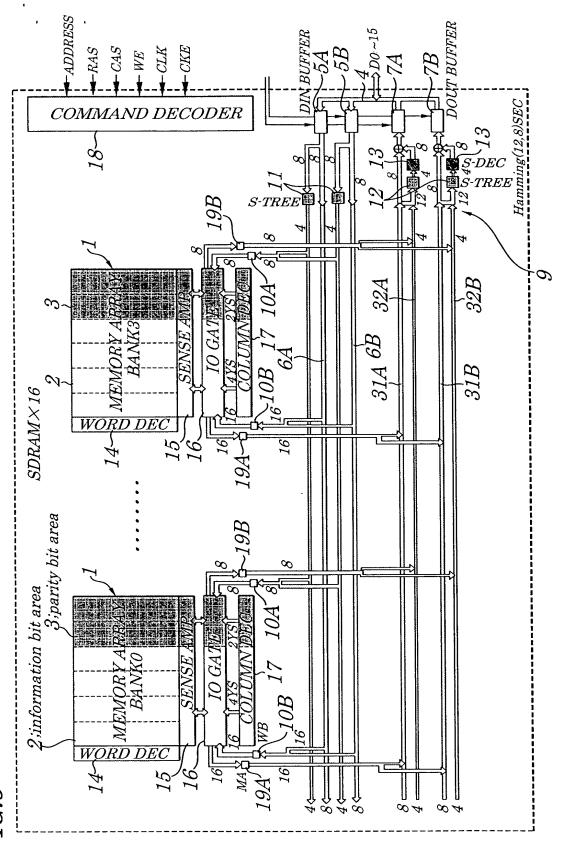


- \odot AND
- \oplus EOR



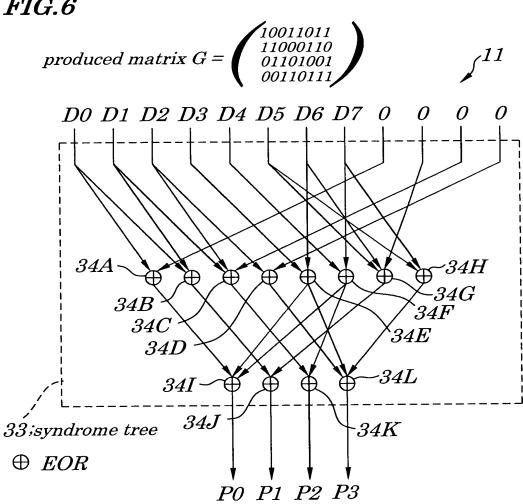


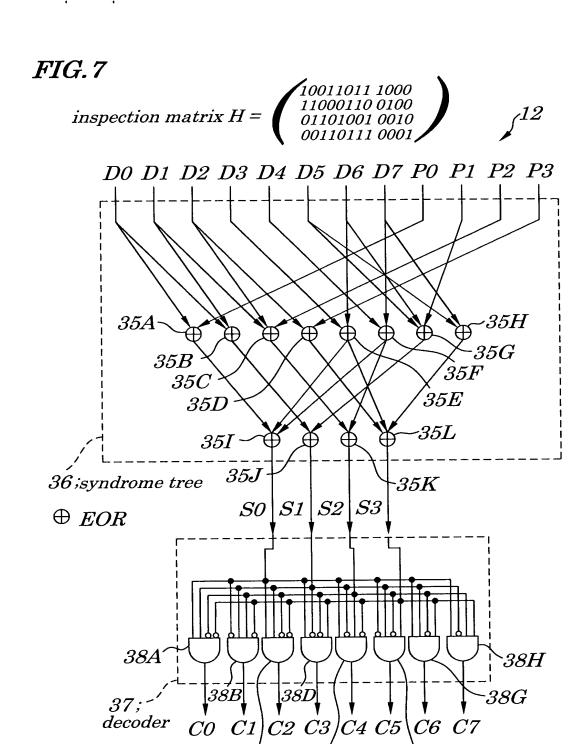
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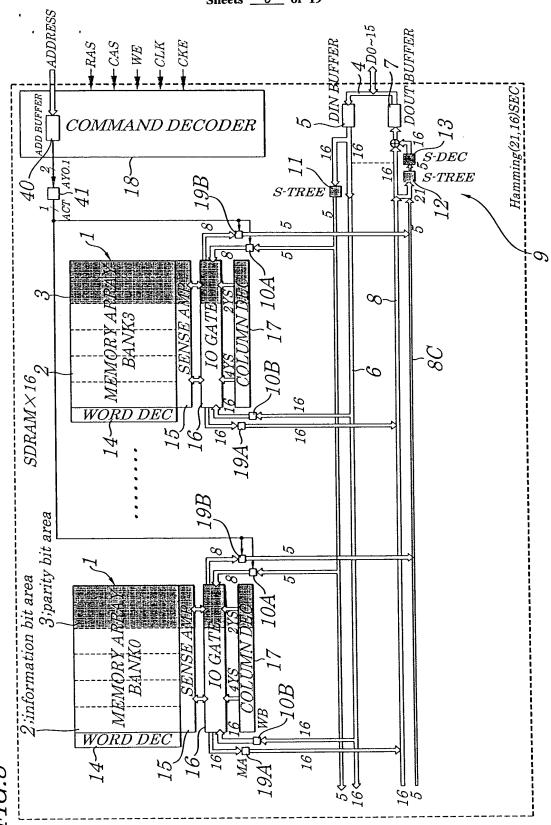
7.1G.5



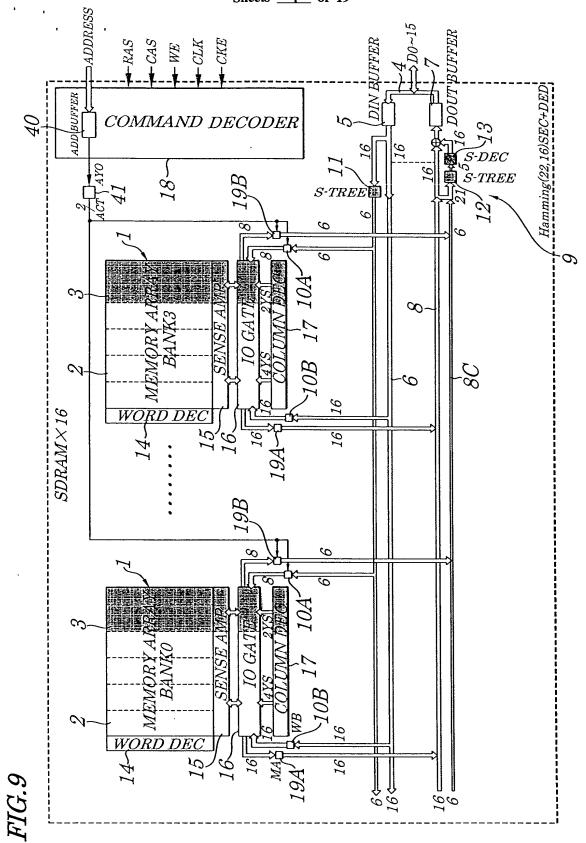




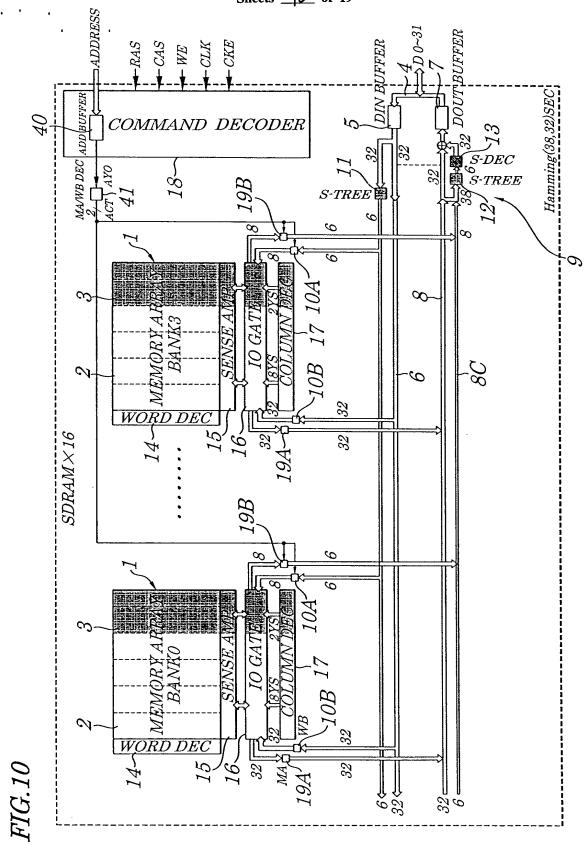
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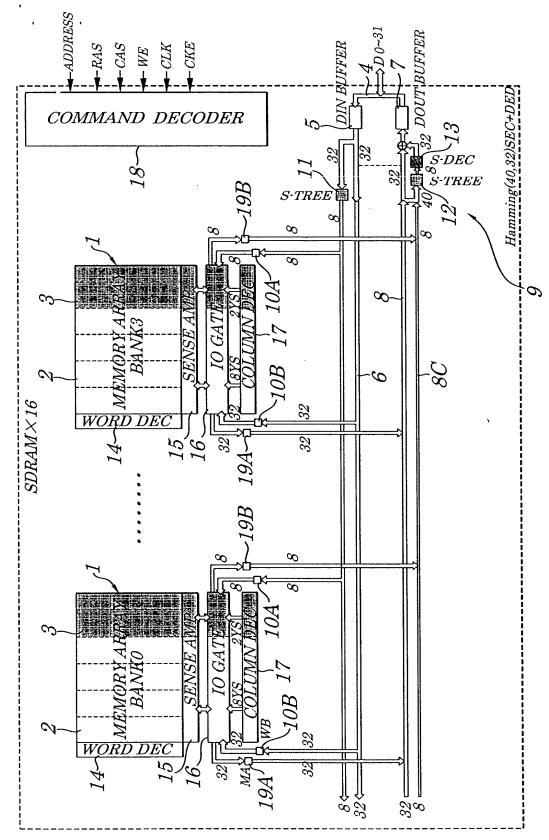


FIG.12

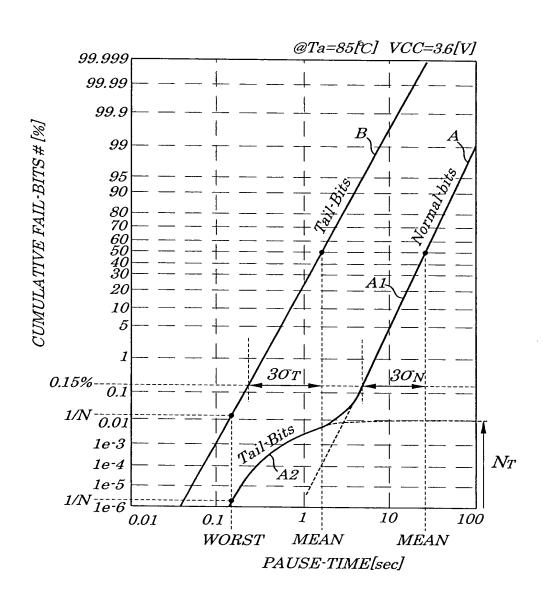
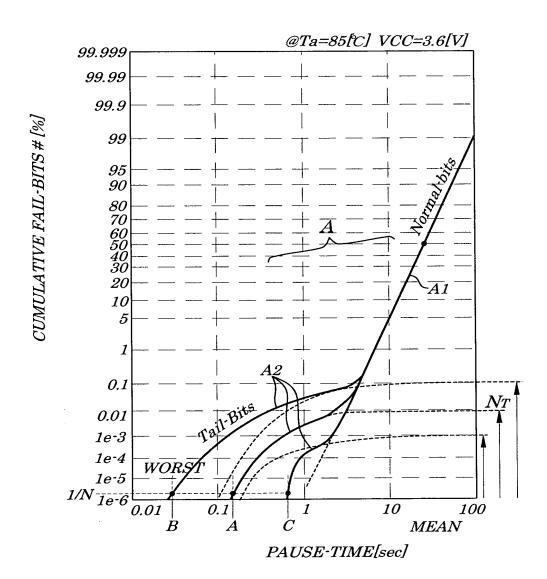
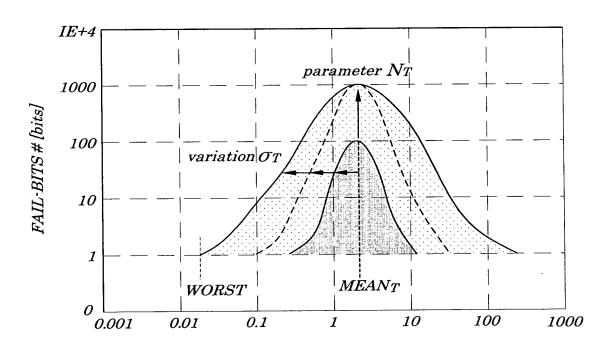


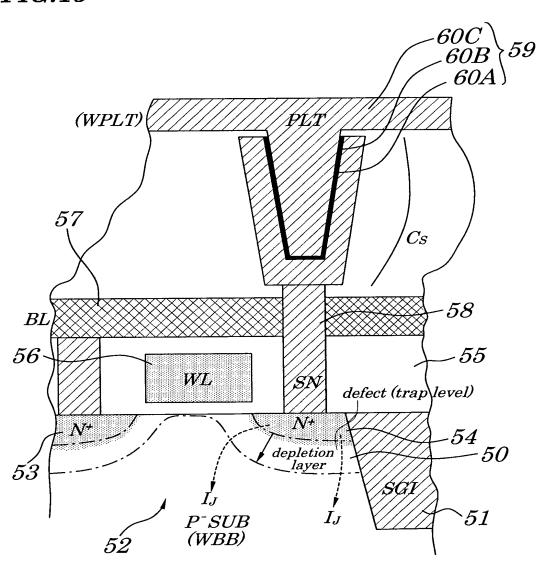
FIG.13





PAUSE-TIME[sec]

FIG.15



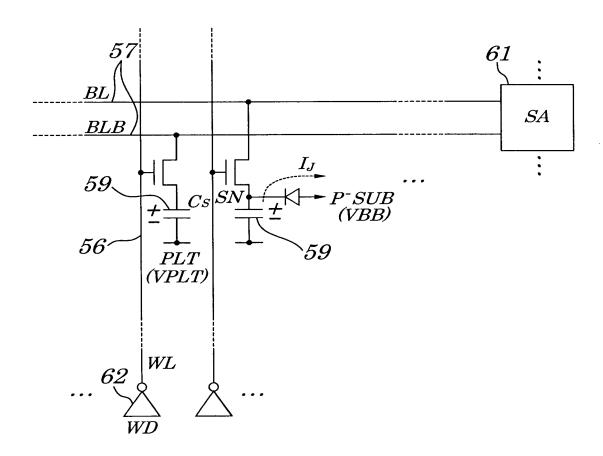
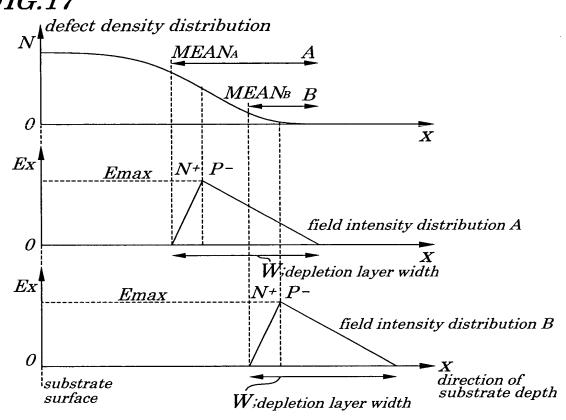
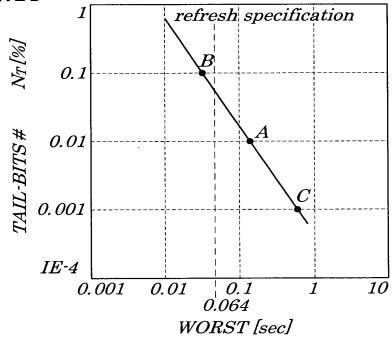
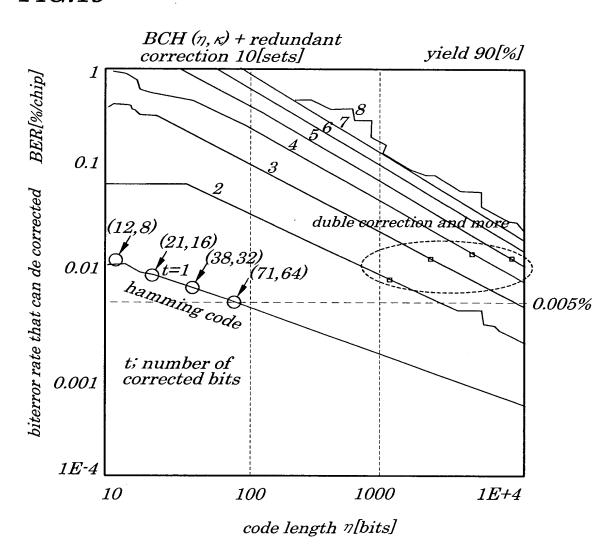


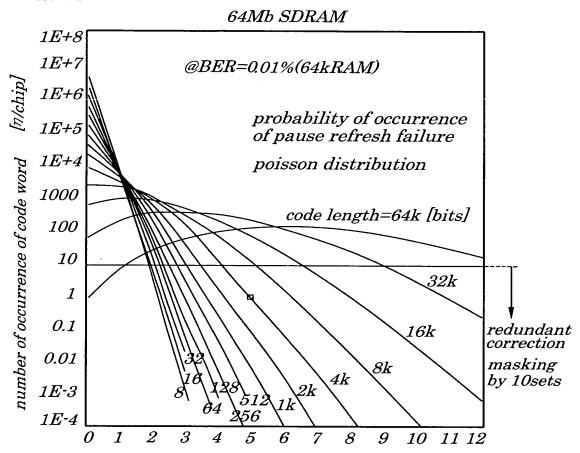
FIG.17











bit number of pause failure per one code word [bits/word]

